# NIKO-SEM

# N-Channel Enhancement Mode Field Effect Transistor

# P0920ATF

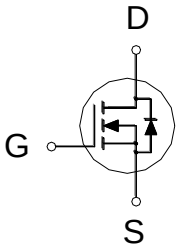
**TO-220F**

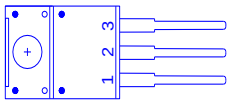
**Halogen-Free & Lead-Free**

RoHS Compliant

## PRODUCT SUMMARY

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ | $I_D$ |
|---|---|---|
| 200V | 0.42Ω | 9A |




1. GATE
2. DRAIN
3. SOURCE

## ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25 °C Unless Otherwise Noted)

| PARAMETERS/TEST CONDITIONS | | SYMBOL | LIMITS | UNITS |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | 200 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current[2] | $T_C$ = 25 °C | $I_D$ | 9 | A |
| | $T_C$ = 100 °C | | 5 | |
| Pulsed Drain Current[1] | | $I_{DM}$ | 22 | |
| Avalanche Current | | $I_{AS}$ | 9 | |
| Avalanche Energy | L = 2.1 mH | $E_{AS}$ | 85 | mJ |
| Power Dissipation | $T_C$ = 25 °C | $P_D$ | 28 | W |
| | $T_C$ = 100 °C | | 11 | |
| Junction & Storage Temperature Range | | $T_J$, $T_{stg}$ | -55 to 150 | °C |

## THERMAL RESISTANCE RATINGS

| THERMAL RESISTANCE | SYMBOL | TYPICAL | MAXIMUM | UNITS |
|---|---|---|---|---|
| Junction-to-Case | $R_{\theta JC}$ | | 4.4 | °C / W |

[1]Pulse width limited by maximum junction temperature.
[2]Limited only by maximum temperature allowed.

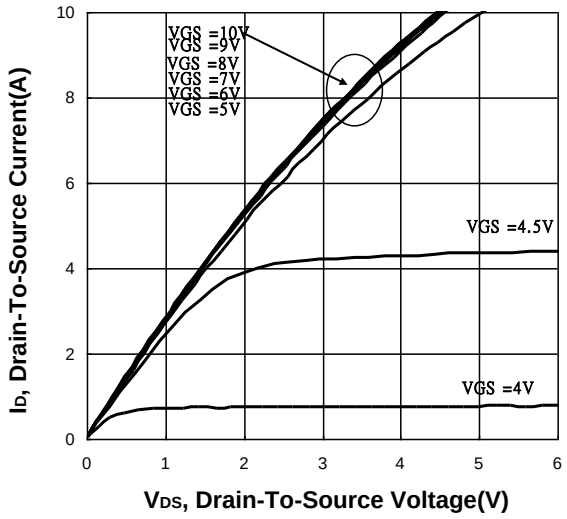
## ELECTRICAL CHARACTERISTICS ($T_J$ = 25 °C, Unless Otherwise Noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | LIMITS | | | UNIT |
|---|---|---|---|---|---|---|
| | | | MIN | TYP | MAX | |
| **STATIC** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0V, $I_D$ = 250μA | 200 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250μA | 2 | 2.6 | 4 | |
| Gate-Body Leakage | $I_{GSS}$ | $V_{DS}$ = 0V, $V_{GS}$ = ±20V | | | ±100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 200V, $V_{GS}$ = 0V | | | 1 | μA |
| | | $V_{DS}$ = 160V, $V_{GS}$ = 0V, $T_J$ = 125 °C | | | 10 | |
| Drain-Source On-State Resistance[1] | $R_{DS(ON)}$ | $V_{GS}$ = 10V, $I_D$ = 4.5A | | 0.3 | 0.42 | Ω |
| Forward Transconductance[1] | $g_{fs}$ | $V_{DS}$ = 10V, $I_D$ = 4.5A | | 19 | | S |

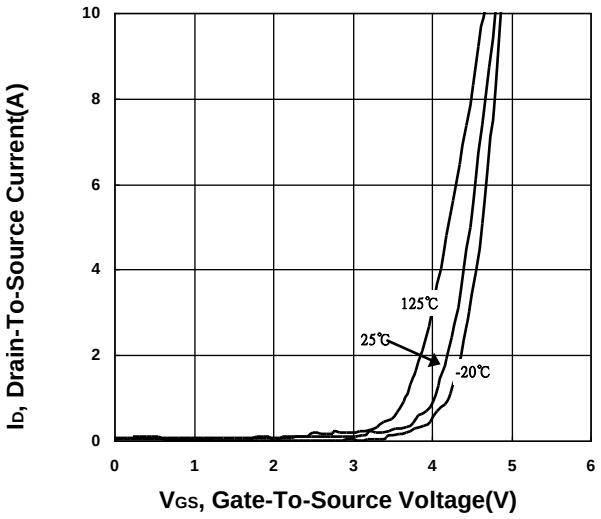
| | | | | | | |
|---|---|---|---|---|---|---|
| **DYNAMIC** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0V, $V_{DS}$ = 25V, f = 1MHz | | 841 | | pF |
| Output Capacitance | $C_{oss}$ | | | 123 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 29 | | |
| Total Gate Charge[2] | $Q_g$ | $V_{DS}$ = 200V, $V_{GS}$ = 10V, $I_D$ = 9A | | 29 | | nC |
| Gate-Source Charge[2] | $Q_{gs}$ | | | 4 | | |
| Gate-Drain Charge[2] | $Q_{gd}$ | | | 13 | | |
| Turn-On Delay Time[2] | $t_{d(on)}$ | $V_{DS}$ = 100V, $I_D \cong$ 9A, $V_{GS}$ = 10V , $R_{GEN}$ = 6Ω | | 11 | | nS |
| Rise Time[2] | $t_r$ | | | 38 | | |
| Turn-Off Delay Time[2] | $t_{d(off)}$ | | | 36 | | |
| Fall Time[2] | $t_f$ | | | 45 | | |
| **SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J$ = 25 °C)** | | | | | | |
| Continuous Current | $I_S$ | | | | 9 | A |
| Forward Voltage[1] | $V_{SD}$ | $I_F$ = 9A, $V_{GS}$ = 0V | | | 1.6 | V |
| Reverse Recovery Time | $t_{rr}$ | $I_F$ = 9A, $dI_F/dt$ = 100A / μS | | 151 | | nS |
| Reverse Recovery Charge | Qrr | | | 779 | | nC |

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

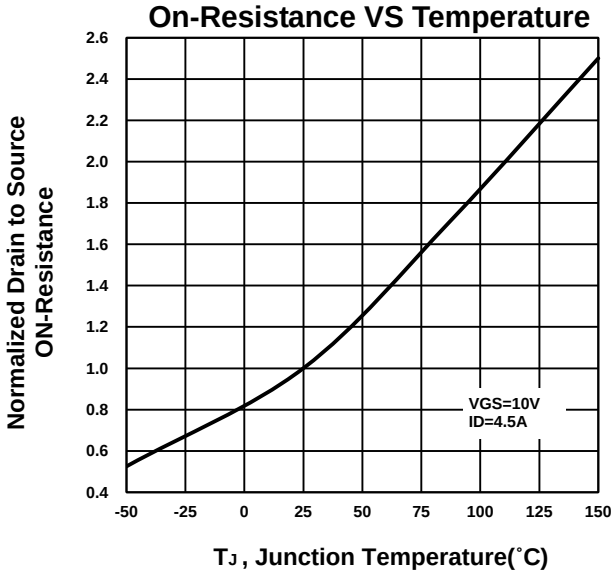
## Output Characteristics



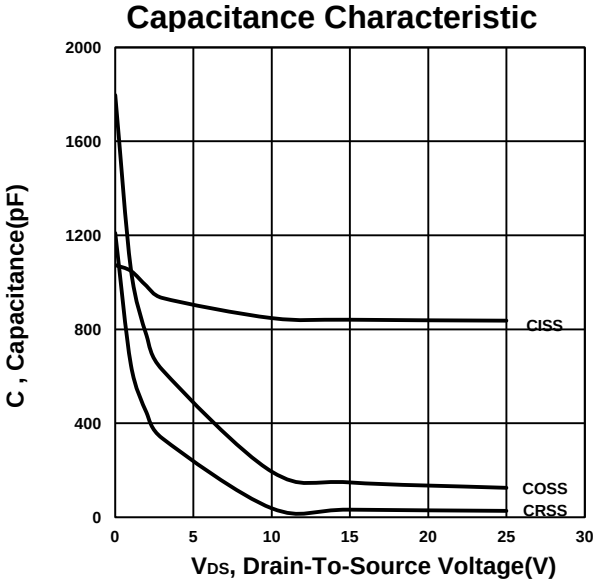

## Transfer Characteristics



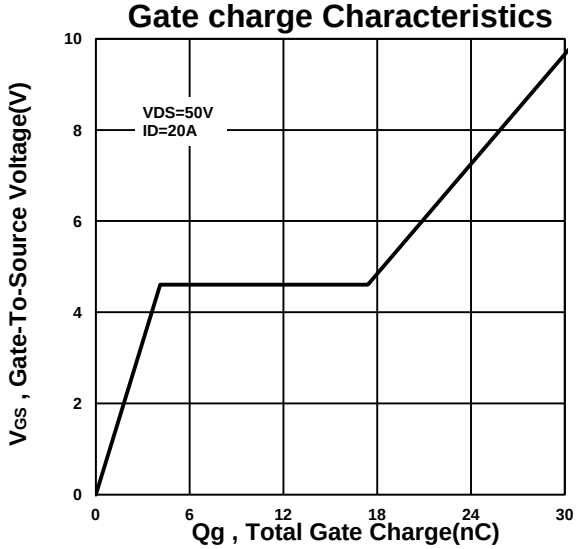

## On-Resistance VS Temperature



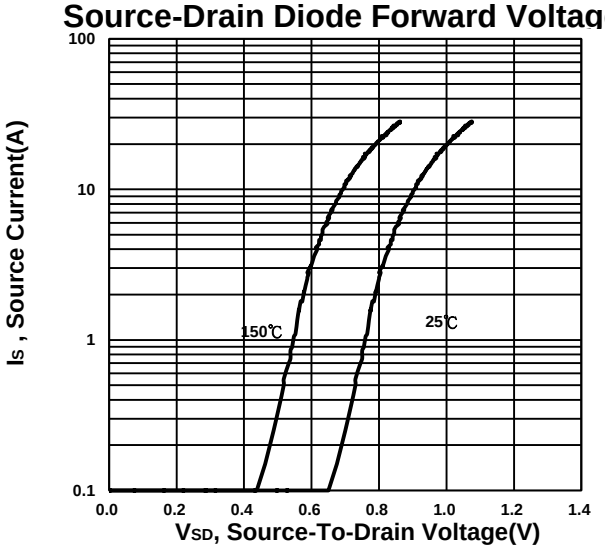

## Capacitance Characteristic



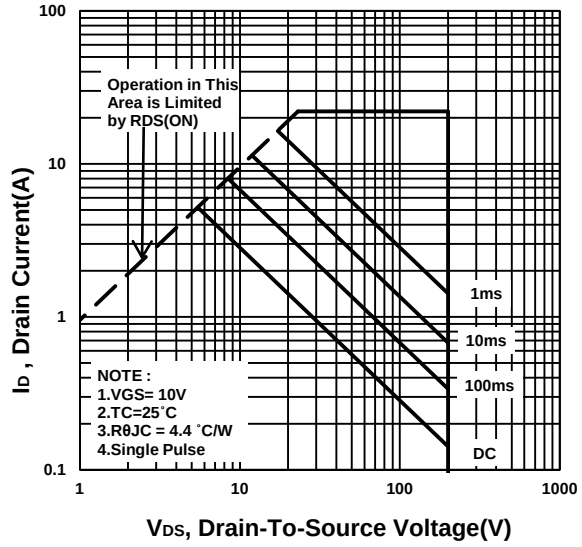

## Gate charge Characteristics



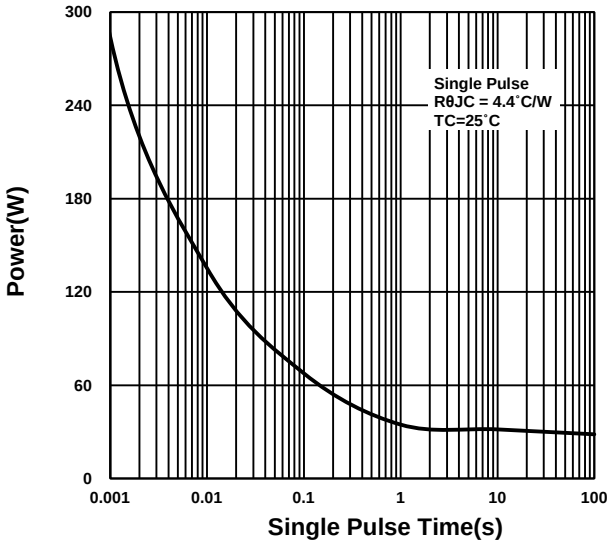

## Source-Drain Diode Forward Voltage



## Safe Operating Area




## Single Pulse Maximum Power Dissipation




## Transient Thermal Response Curve